

Binding energy (eV)

860

850

840

830

$[\times 10^4]$

Photoelectron intensity (count)

Ni 2p (SUS304)

Source : Ga (9251.7 eV)
8380 eV-8420 eV / 0.2 eV
pass : 200 eV
dwell : 200 ms
sweep : 20
slit : 400 (0.5 mm)
Exp time : 20 min

1.5

1

0.5

8380

8390

8400

8410

8420

Kinetic energy (eV)

